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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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Slotted Optical Switch

OPB852A1-3

OPB853A1-3

Features:

- Inexpensive opaque plastic housing
- Choice of transistor (OPB852) or photodarlington (OPB853) output
- 0.125" (3.18 mm) slot width
- 0.290" (7.37 mm) lead spacing
- Apertured for high resolution





Description:

Slotted optical switches in the OPB852, and OPB853 series consist of an infrared emitting diode and a NPN silicon phototransistor or photodarlington, mounted on opposite sides of a 0.125" (3.175 mm) wide slot. The OPB852A, OPB852B and OPB852C have phototransistor output, while the OPB853A, OPB853B and OPB853C have photodarlington output.

On each of these devices, the emitter has a molded-in aperture of $0.050'' \times 0.050'' (1.270 \text{ mm x } 1.270 \text{ mm})$ and the phototransistor (OPB852) or photodarlington (OPB853) has a molded-in aperture of $0.010'' \times 0.050'' (0.254 \text{ mm x } 1.270 \text{ mm})$.

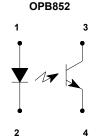
Phototransistor or photodarlington switching occurs when an opaque object passes through the slot.

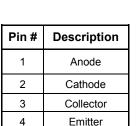
Applications:

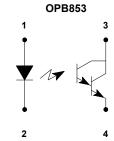
- Non-contact interruptive object sensing
- Assembly line automation
- Machine automation
- Equipment security
- Machine safety

	OPB853A1
- [24.63±0.25] .970±.01	OPB853A2
PIN #1 [19.05±0.13]	OPB853A3
[3.18±0.13] .125±.005	
OPTICAL Q [12.32±0.25] [3.30] [2.92] .130	
.110 NOM .115	
[2.03±0.25] .080±.01	
.,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	
[2.54±0.13] .100±.005	
[8.89] .350 X	
[7.37±0.25] .290±.01	
DIMENSIONS ARE IN:	MILLIMETERS] ICHES
[6.35±0.25] 2 [2.54±0.13] .250±.01 1 [2.54±0.05]	

Part Number	LED Peak Wavelength	Sensor	Slot Width/ Depth	Aperture Emitter/ Sensor	Lead Length / Spacing
OPB852A1					
OPB852A2		Transistor		0.05" / 0.01"	0.425" / 0.290"
OPB852A3	890 nm		0.120" /		
OPB853A1	690 11111		0.315"		
OPB853A2		Darlington			
OPB853A3					









General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

Slotted Optical Switch

OPB852A1-3, OPB853A1-3



Electrical Specifications

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Storage & Operating Temperature Range	-40°C to +85° C
Lead Soldering Temperature [1/16 inch (1.6mm) from the case for 5 sec. with soldering iron]	260° C ⁽¹⁾
Input Diode	
Forward DC Current	40 mA

Forward DC Current	40 mA
Peak Forward Current (1 μs pulse width, 300 pps)	3 A
Reverse DC Voltage	2 V
Power Dissipation	100 mW ⁽²⁾

Output Phototransistor

Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5 V
Power Dissipation	100 mW ⁽²⁾

Electrical Characteristics (T_A = 25°C unless otherwise noted)

	SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Input Diade (see OP140 for additional information—OPRSS2A OP245 for additional information—OPRSS3A)							

Input Diode (see OP140 for additional information—OPB852A_, OP245 for additional information—OPB853A

V _F	Forward Voltage	-	1	1.7	V	I _F = 20 mA
I _R	Reverse Current	-	-	100	μΑ	V _R = 2 V

Output Phototransistor (see OP550 for additional information—OPB852A_, OP565 for additional information—OPB853A)

V _{(BR)CEO}	Collector-Emitter Breakdown Voltage OPB852A1, OPB852A2, OPB852A3 OPB853A1, OPB853A2, OPB853A3	30 15	- -	- -	V V	I _C = 1 mA I _C = 1 mA
$V_{(BR)ECO}$	Emitter-Collector Breakdown Voltage	5	-	-	V	I _E = 100 μA
I _{CEO}	Collector-Emitter Dark Current	-	-	100	nA	V _{CE} = 10 V

Combined

$V_{\text{CE(SAT)}}$	Saturation Voltage OPB852A1, OPB852A2 OPB852A3 OPB853A1, OPB853A2, OPB853A3	- - -	- - -	0.4 0.4 1.0	V V V	I _C = 500 μA, I _F = 20 mA I _C = 1.8 mA, I _F = 20 mA I _C = 1.8 mA, I _F = 10 mA
I _{C(ON)}	On-State Collector Current OPB852A1 OPB852A2 OPB852A3 OPB853A1 OPB853A2 OPB853A3	1.0 2.0 4.0 2.5 5.0 10.0			mA mA mA mA mA	$V_{CE} = 5 \text{ V}, I_F = 20 \text{ mA}$ $V_{CE} = 5 \text{ V}, I_F = 20 \text{ mA}$ $V_{CE} = 5 \text{ V}, I_F = 20 \text{ mA}$ $V_{CE} = 1.5 \text{ V}, I_F = 5 \text{ mA}$ $V_{CE} = 1.5 \text{ V}, I_F = 5 \text{ mA}$ $V_{CE} = 1.5 \text{ V}, I_F = 5 \text{ mA}$ $V_{CE} = 1.5 \text{ V}, I_F = 5 \text{ mA}$

Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- (2) Derate linearly 1.67 mW/° C above 25° C.
- (3) Methanol and isopropanol are recommended as cleaning agents. Housings are soluble in chlorinated hydrocarbons and ketones. Highly activated, water soluble fluxes may attack housings in some situations.
- (4) All parameters tested using pulse technique.

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OPB852A1-3, OPB853A1-3



Performance

